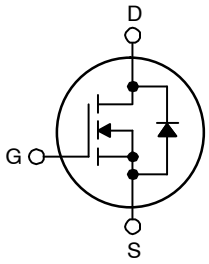
MOSFET – N-Channel, QFET

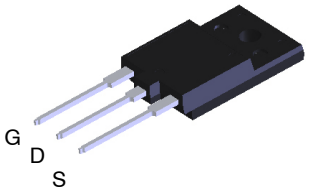
900 V, 7.0 A, 1.1 Ω

FQAF11N90C

V_{DSS}	$R_{DS(on)}$ MAX	I_D MAX
900 V	1.1 Ω @ 10 V	7.0 A



N-CHANNEL MOSFET



TO−3PF−L
CASE 340AH

Description

This N−Channel enhancement mode power MOSFET is produced using **onsemi**'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on−state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 7.0 A, 900 V, $R_{DS(on)}$ = 1.1 Ω (Max.) @ V_{GS} = 10 V, I_D = 3.5 A
- Low Gate Charge (Typ. 60 nC)
- Low C_{rss} (Typ. 23 pF)
- 100% Avalanche Tested
- This is a Pb−Free Device

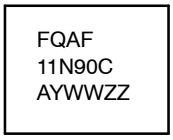
ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DSS}	Drain−Source Voltage	900	V
I_D	Drain Current – Continuous (T_C = 25°C) – Continuous (T_C = 100°C)	7.0 4.4	A A
I_{DM}	Drain Current – Pulsed (Note 1)	28.0	A
V_{GSS}	Gate−Source Voltage	±30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	960	mJ
I_{AR}	Avalanche Current (Note 1)	7.0	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	12	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.0	V/ns
P_D	Power Dissipation (T_C = 25°C) – Derate Above 25°C	120 0.96	W W/°C
T_J, T_{STG}	Operating and Storage Temperature Range	−55 to +150	°C
T_L	Maximum Lead Temperature for Soldering Purposes, 1/8″ from Case for 5 seconds	300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. L = 37 mH, I_{AS} = 7.0 A, V_{DD} = 50 V, R_G = 25 Ω, Starting T_J = 25 °C.
3. I_{SD} ≤ 11.0 A, di/dt ≤ 200 A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25 °C.

MARKING DIAGRAM



FQAF11N90	= Specific Device Code
A	= Assembly Plant Code
YWW	= Date Code (Year & Week)
ZZ	= Lot Code

ORDERING INFORMATION

Device	Package	Shipping
FQAF11N90C	TO−3PF (Pb−Free)	30 Units / Tube

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction−to−Case, Max.	1.04	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient, Max.	40	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain−Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA,	900	–	–	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	–	1.00	–	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 900 V, V_{GS} = 0 V	–	–	10	μA
		V_{DS} = 720 V, T_C = 125°C	–	–	100	μA
I_{GSSF}	Gate−Body Leakage Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V	–	–	100	nA
I_{GSSR}	Gate−Body Leakage Current, Reverse	V_{GS} = −30 V, V_{DS} = 0 V	–	–	−100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	3.0	–	5.0	V
$R_{DS(on)}$	Static Drain−Source On−Resistance	V_{GS} = 10 V, I_D = 3.5 A	–	0.91	1.1	Ω
g_{FS}	Forward Transconductance	V_{DS} = 50 V, I_D = 3.5 A	–	–	–	S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz	–	2530	3290	pF
C_{oss}	Output Capacitance		–	215	280	pF
C_{rss}	Reverse Transfer Capacitance		–	23	30	pF
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 450 V, I_D = 11.0 A, R_G = 25 Ω (Note 4)	–	60	130	ns
t_r	Turn−On Rise Time		–	130	270	ns
$t_{d(off)}$	Turn-Off Delay Time		–	130	270	ns
t_f	Turn−Off Fall Time		–	85	180	ns
Q_g	Total Gate Charge	V_{DS} = 720 V, I_D = 11.0 A, V_{GS} = 10 V (Note 4)	–	60	80	nC
Q_{gs}	Gate−Source Charge		–	13	–	nC
Q_{gd}	Gate−Drain Charge		–	25	–	nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
I_S	Maximum Continuous Drain−Source Diode Forward Current		–	–	7.0	A
I_{SM}	Maximum Pulsed Drain−Source Diode Forward Current		–	–	28.0	A
V_{SD}	Drain−Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 7.0 A	–	–	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = 11.0 A, dI_F/dt = 100 A/μs	–	1000	–	ns
Q_{rr}	Reverse Recovery Charge		–	17.0	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially Independent of Operating Temperature.

TYPICAL CHARACTERISTICS

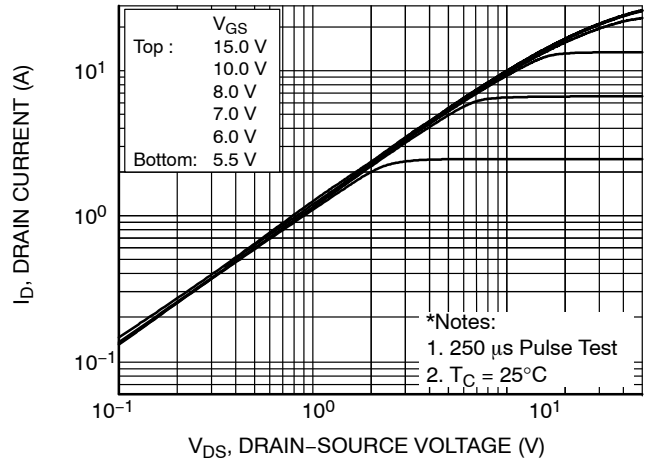


Figure 1. On−Region Characteristics

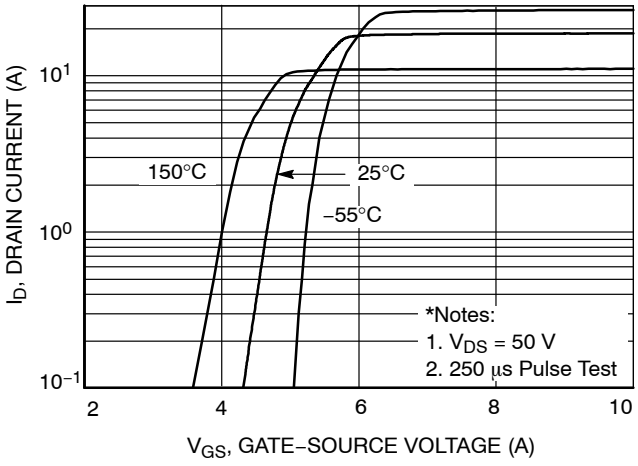


Figure 2. Transfer Characteristics

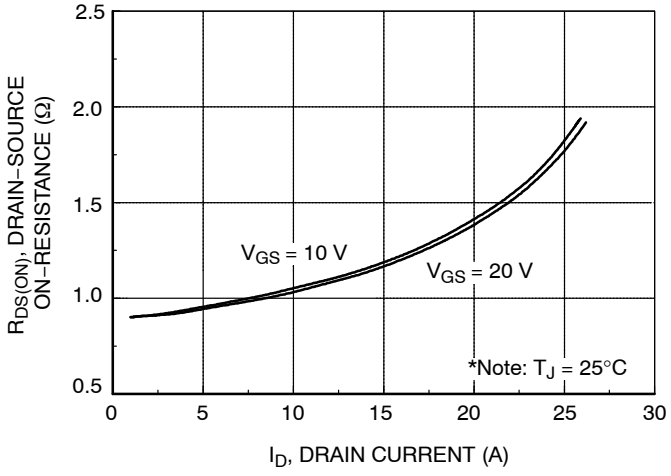


Figure 3. On−Resistance Variation vs. Drain Current and Gate Voltage

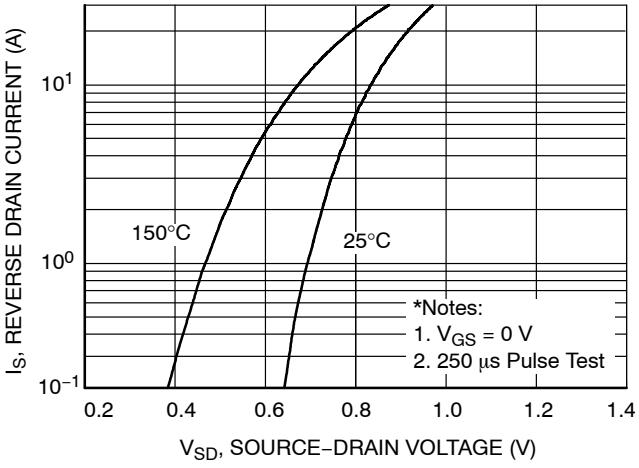


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

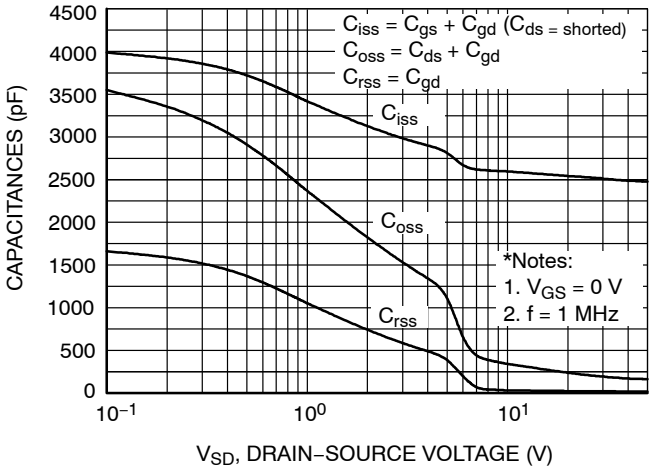


Figure 5. Capacitance Characteristics

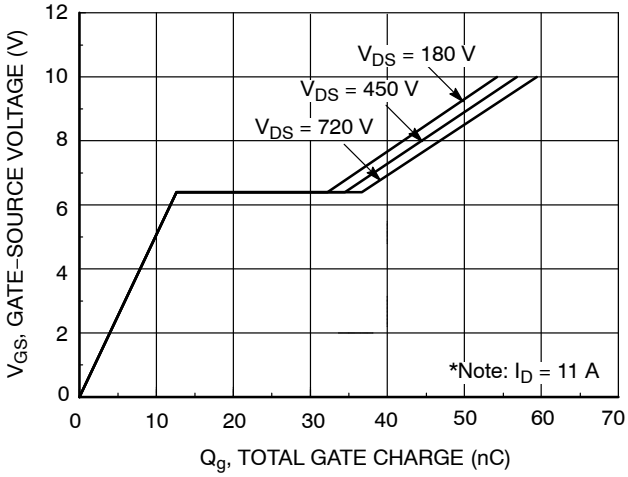


Figure 6. Gate Charge Characteristics

TYPICAL CHARACTERISTICS (CONTINUED)

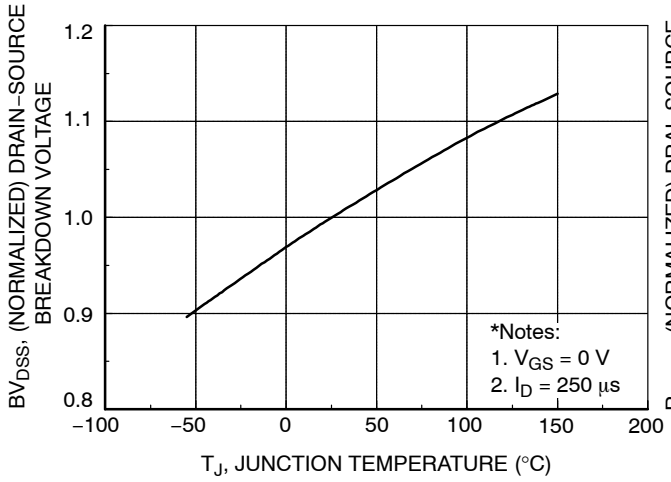


Figure 8. Breakdown Voltage Variation vs. Temperature

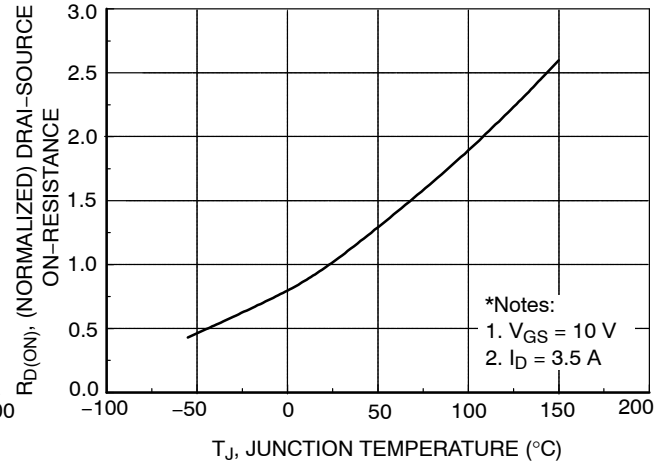


Figure 9. On−Resistance Variation vs. Temperature

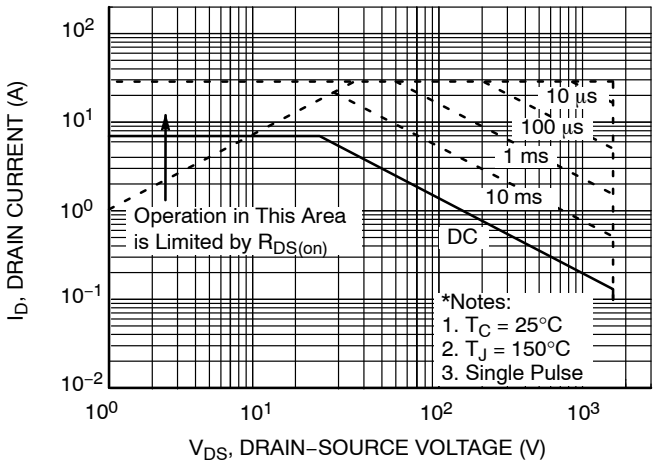


Figure 10. Maximum Safe Operating Area

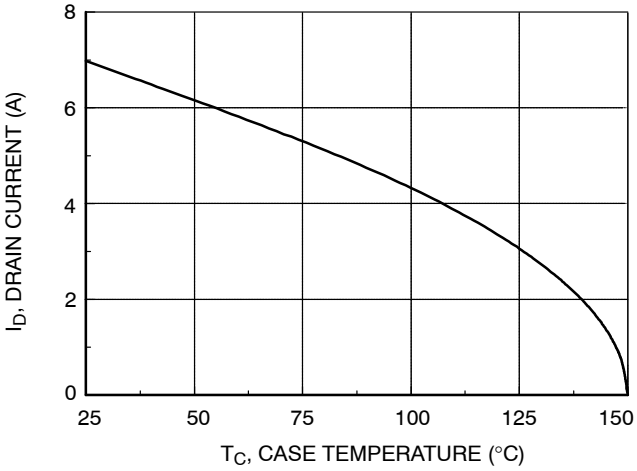


Figure 11. Maximum Drain Current vs. Case Temperature

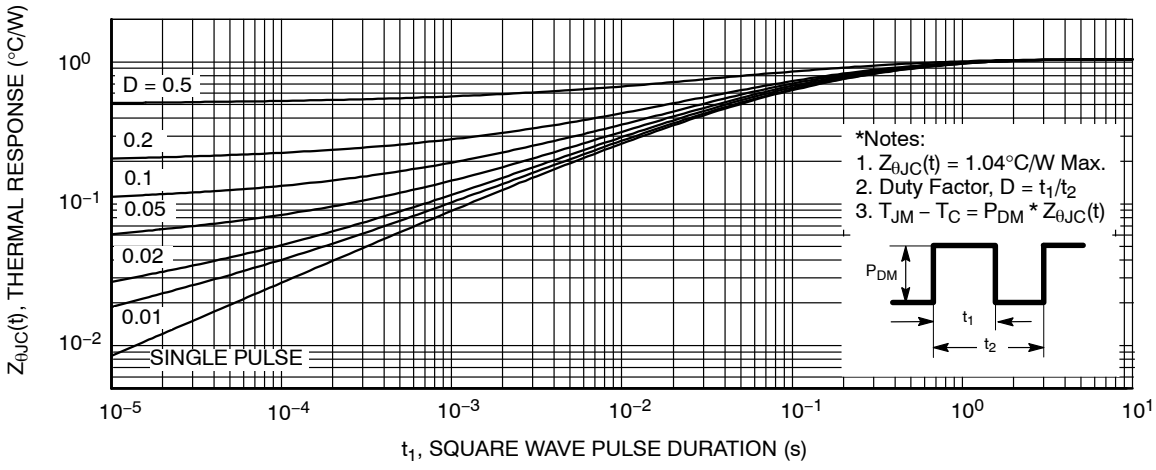


Figure 7. Transient Thermal Response Curve

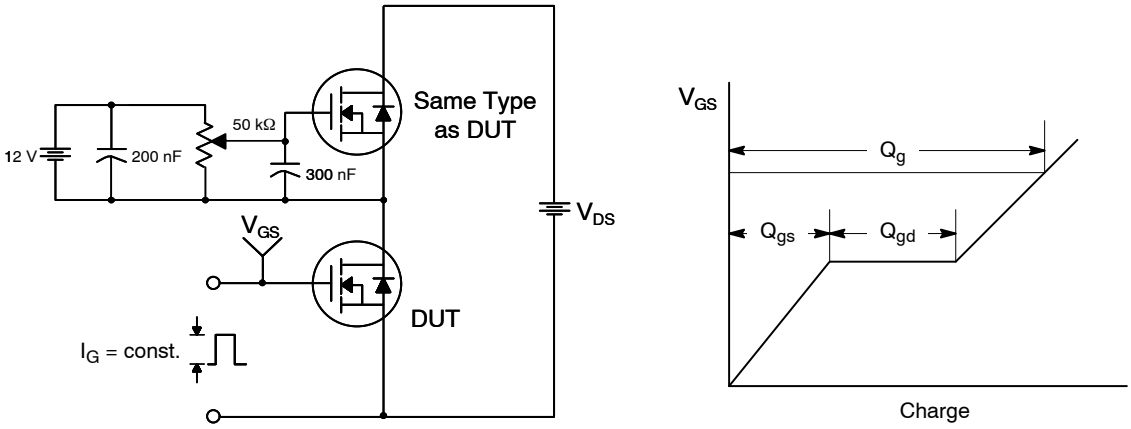


Figure 12. Gate Charge Test Circuit & Waveform

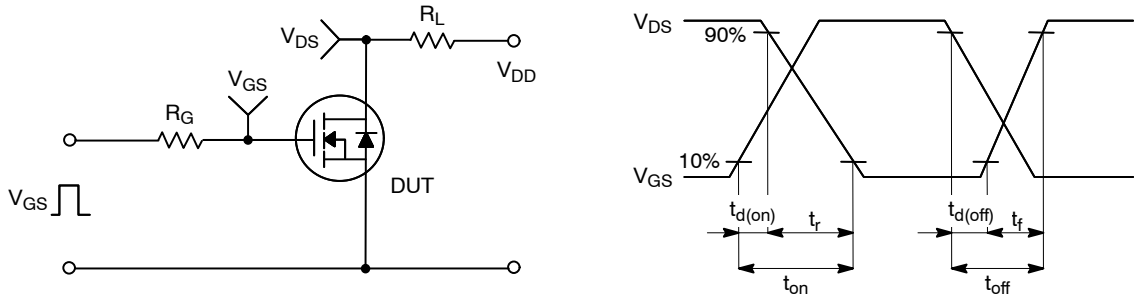


Figure 13. Resistive Switching Test Circuit & Waveforms

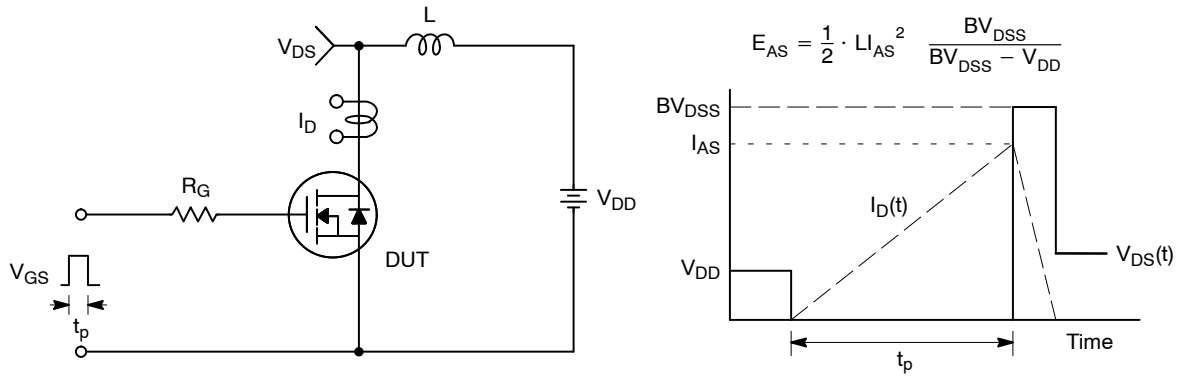


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

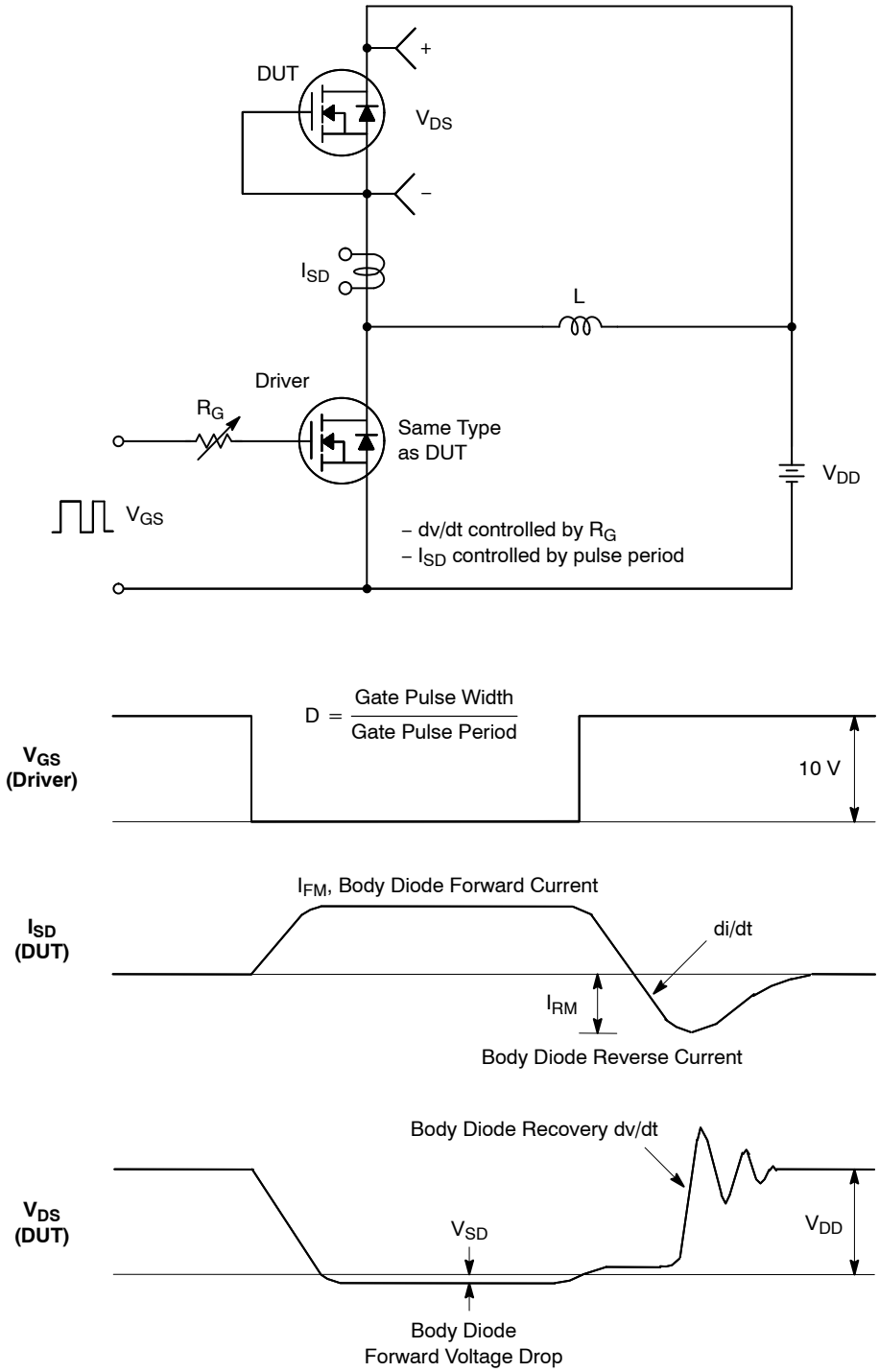
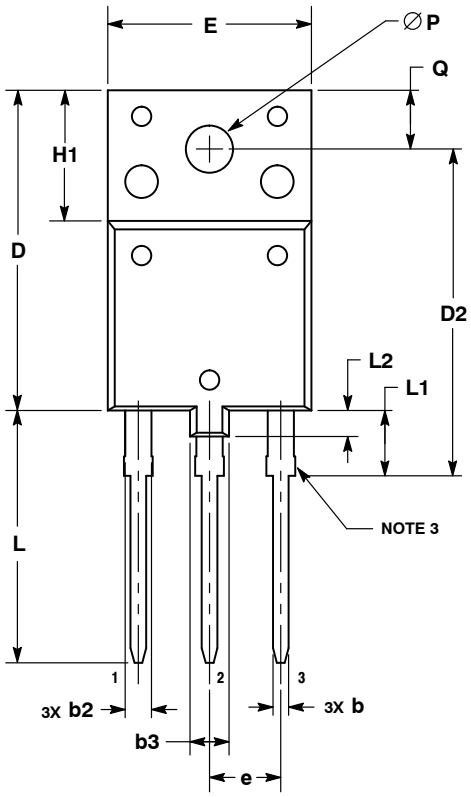
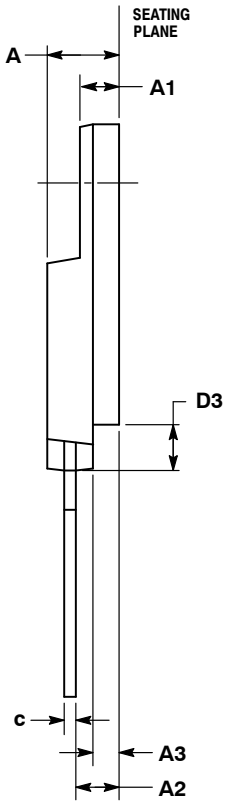


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

TO−3PF−3L
CASE 340AH
ISSUE A

DATE 09 JAN 2015





NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR UNCONTROLLED IN THIS AREA (6 PLACES).
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY.
5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.20.

	MILLIMETERS	
DIM	MIN	MAX
A	5.30	5.70
A1	2.80	3.20
A2	3.10	3.50
A3	1.80	2.20
b	0.65	0.95
b2	1.90	2.15
b3	3.80	4.20
c	0.80	1.10
D	24.30	24.70
D2	24.70	25.30
D3	3.30	3.70
E	15.30	15.70
e	5.35	5.55
H1	9.80	10.20
L	19.10	19.50
L1	4.80	5.20
L2	1.90	2.20
P	3.40	3.80
Q	4.30	4.70

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